

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	721	73/863.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 11:10
L2	156	73/863.82.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:40
L3	241	73/864.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:40
L4	432	73/864.91.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:40
L5	219	73/1.02.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:41
L6	0	1 and (sample near4 (receiving near4 chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:41
L7	0	2 and (sample near4 (receiving near4 chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:41
L8	0	3 and (sample near4 (receiving near4 chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:41

L9	0	4 and (sample near4 (receiving near4 chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:41
L10	1	5 and (sample near4 (receiving near4 chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 09:43
L11	66	(sample near4 (receiving near4 chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:25
L12	20	11 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:26
L13	16	12 and (fluid or liquid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:34
L14	11	13 and processor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:05
L15	2	14 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:05
L16	4	14 and (electrical near4 properties)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:45

L17	2974	osmometry	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:06
L18	4	11 and 17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:06
L19	1	17 and 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:07
L20	18	("5851489").URPN.	USPAT	OR	ON	2005/12/23 10:25
L21	2501	osmolarity	USPAT	OR	ON	2005/12/23 10:25
L22	0	11 and 21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:25
L23	332	21 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10
L24	276	23 and sample	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:26
L25	0	24 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:26
L26	0	21 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:27

L27	2	11 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:27
L28	7	("3322504"   "3572892"   "4209299"   "4974952"   "5030418"   "5278048").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/23 10:33
L29	15328	(sample near4 (space or cell or chip or region)) and electrode	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/23 12:05
L30	11460	29 and (fluid or liquid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:34
L31	34	30 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:34
L33	13	31 and (electrical near4 properties)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:47
L34	1	33 and calibrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 10:46
L35	3	33 and (calibration or calibrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:11
L36	529	73/61.41.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 11:10

L37	161	73/64.56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 11:10
L38	418	324/130.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 11:10
L39	24	36 and 29	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/23 12:05
L40	7	37 and 29	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/23 12:05
L41	1	38 and 29	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/23 12:05
L42	0	39 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10
L43	0	40 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:05
L44	0	41 and (intrinsic near4 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:05
L45	9	39 and conductivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10
L46	3	40 and conductivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10

L47	1	41 and conductivity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10
L48	9	45 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10
L49	3	46 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10
L50	1	47 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:10
L51	8	48 and (calibration or calibrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:12
L52	1	49 and (calibration or calibrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:11
L53	1	50 and (calibration or calibrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/23 12:12